

ABSTRACT OF THE DISCLOSURE

A semiconductor device disclosed herein comprises: a first base region which is of a first conductivity type; a second base region which is of a second conductivity type and which is selectively formed on a major surface of the first base region; 5 a stopper region which is of a first conductivity type and which is formed on the major surface of the first base region, the stopper region being a predetermined distance away from the second base region and surrounding the second base region; and a ring region 10 which is of a second conductivity type which is formed on the major surface of the first base region between the second base region and the stopper region, the ring region being spirally around the second base region and electrically connected to the second base region and the stopper region.